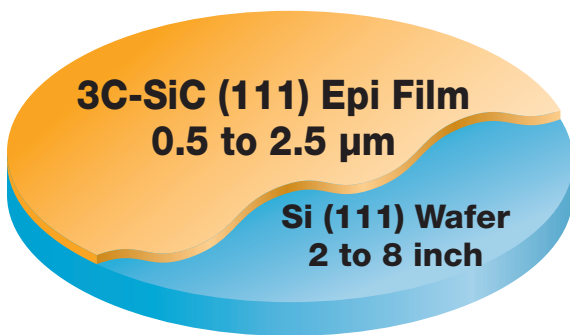


3C-SiC/Si Heteroepitaxial substrates for GaN

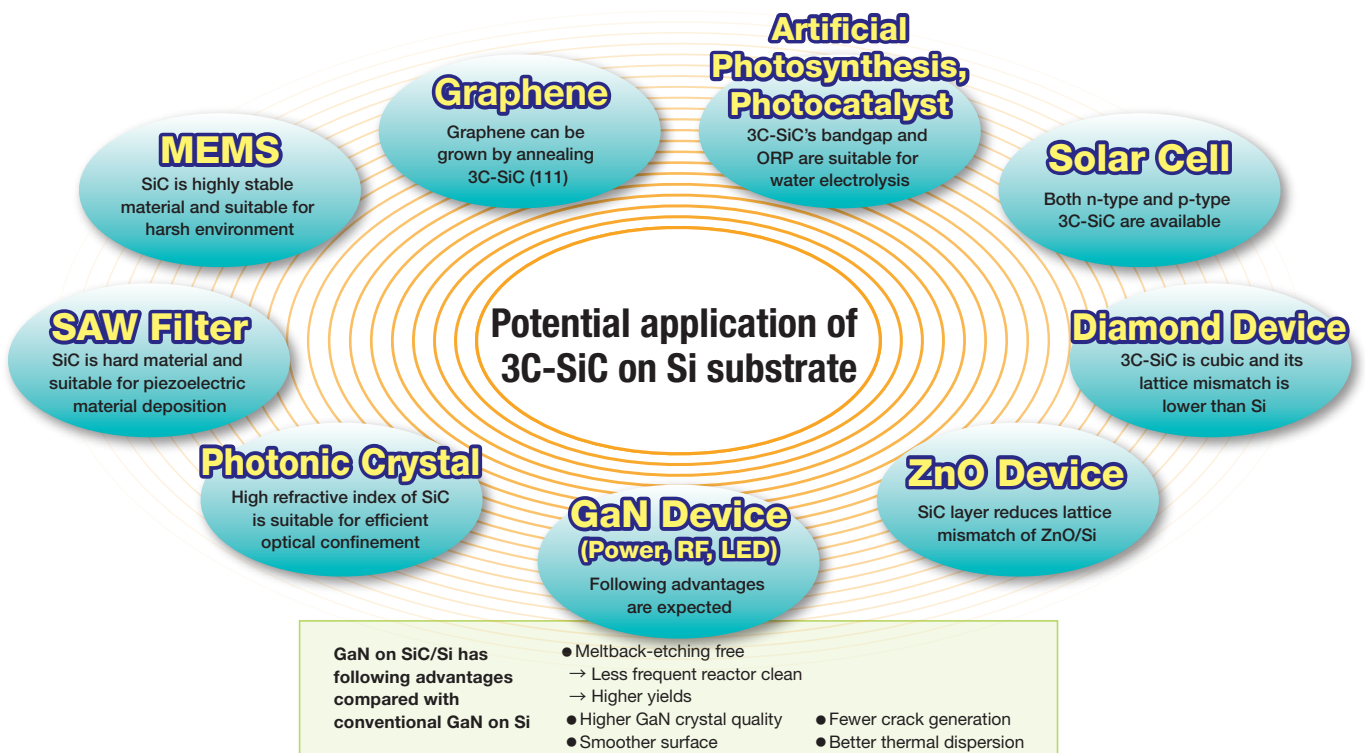
AWI 3C-SiC (111) /Si heteroepitaxial wafers using AW-original epitaxial technologies are one of the most suitable substrates for GaN devices. The 3C-SiC heteroepitaxial technology can realize large diameter substrates, on which high quality GaN layers can be easily grown using simple buffers.

▶ A schematic cross section of AWI 3C-SiC/Si heteroepitaxial wafers for GaN



▶ Specification of 3C-SiC/Si wafers

Diameter	2" to 8" diameter
Epi film	0.5 to 2.5 μm-thick SiC (111) layer
Crystal	XRC-FWHM (SiC (111), ω -scan) < 1,600 arcsec @ 1 μm, < 900 arcsec @ 2.5 μm
Applications	GaN-power, GaN-RF and so on.



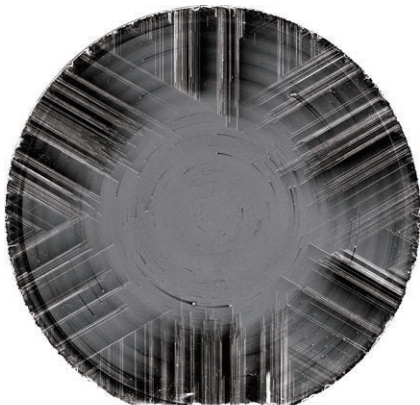
3C-SiC/Si Heteroepitaxial substrates for GaN

An example of AW original GaN HEMT on 6" 3C-SiC/Si substrates

▶ Comparison of 6" thick GaN on Si and 6" thick GaN on SiC/Si

Laser scattering images (Nitride thickness: 8 μm)
No crack available at thick GaN film deposition

GaN on Si



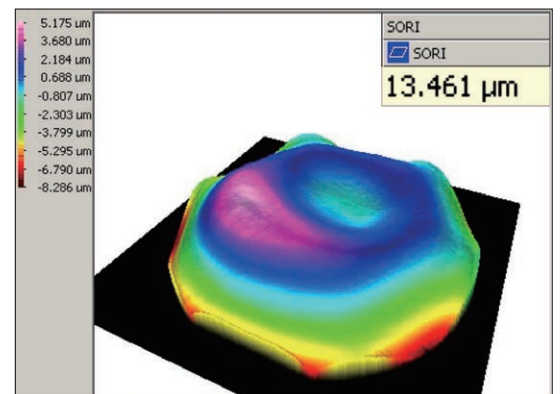
GaN on SiC/Si



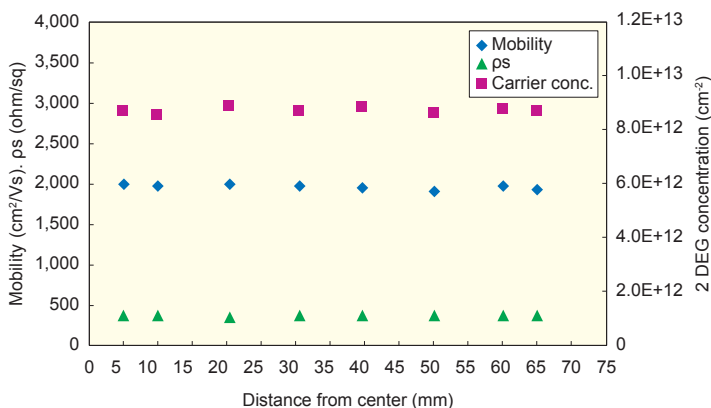
▶ SORI control of 6" thick GaN on SiC/Si

Sori evaluation result (Nitride thickness: 8 μm)
Sori control available at GaN film deposition

GaN on SiC/Si



▶ Electron mobility, Sheet resistance, Carrier conc. of AW original GaN HEMT on 6" 3C-SiC/Si substrates



▶ Vertical I-V characteristic of AW original GaN HEMT on 6" 3C-SiC/Si substrates

